

High Output Current, Rail-to-Rail Input/Output Dual CMOS Operational Amplifier

■ GENERAL DESCRIPTION

The **NJU77902** is a Rail-to-Rail input and output dual CMOS operational amplifier that features high output current drive.

This device is stable to capacitive load and can charge and discharge capacitance quickly by high output current up to 1000mA. In addition, it is ideal for buffer amplifiers as the output stage can supply a respectable amount of current with minimal headroom from either rail.

■ PACKAGE OUTLINE



NJU77902KW2
(ESON8-W2)

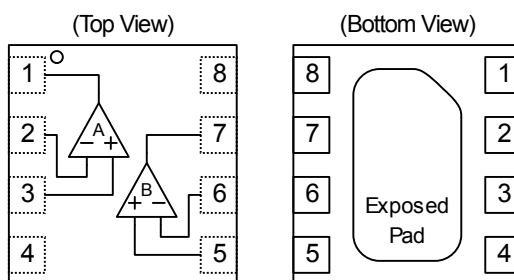
■ FEATURES

- Output Peak Current 1000mA (typ.)
- Rail-to-Rail Input/Output
- Wide Operating Voltage 6V to 18V
- Slew Rate 9V/μs (typ.)
- Package ESON8-W2 (3.0mm x 3.0mm)
- Enhanced RF Noise Immunity
- CMOS Process

■ APPLICATION

- TFT-LCD panel V_{COM} driver
- Instrument Control Voltage Source

■ PIN CONFIGURATION



NJU77902KW2

PIN FUNCTION

1. A OUTPUT
2. A -INPUT
3. A +INPUT
4. V_{SS}
5. B +INPUT
6. B -INPUT
7. B OUTPUT
8. V_{DD}

About Exposed Pad

Connect the Exposed Pad on the V_{SS} .

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise noted.)

PARAMETER	SYMBOL	RATINGS	UNIT
Supply Voltage	V _{DD}	+20	V
Power Dissipation	P _D	560(Note1), 750(Note2), 910(Note3), 2500(Note4)	mW
Output Peak Current	I _{OP}	1000	mA
Input Common Mode Voltage	V _{ICM}	V _{SS} -0.3 to V _{DD} +0.3	V
Differential Input Voltage	V _{ID}	18 (Note5)	V
Operating Temperature Range	T _{opr}	-40 to +85	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

(Note1) Mounted on glass epoxy board. (101.5×114.5×1.6mm: based on EIA/JEDEC standard, 2Layers FR-4)

(Note2) Mounted on glass epoxy board. (101.5×114.5×1.6mm: based on EIA/JEDEC standard, 2Layers FR-4, with Exposed Pad)

(Note3) Mounted on glass epoxy board. (101.5×114.5×1.6mm: based on EIA/JEDEC standard, 4Layers FR-4)

(Note4) Mounted on glass epoxy board. (101.5×114.5×1.6mm: based on EIA/JEDEC standard, 4Layers FR-4, with Exposed Pad)

(For 4Layers: Applying 99.5×99.5mm inner Cu area and a thermal via hole to a board based on JEDEC standard JESD51-5)

(Note5) For supply voltage less than 18V, the absolute maximum rating is equal to the supply voltage.

■ RECOMMENDED OPERATING CONDITION (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V _{DD}	6.0 to 18.0	V

■ ELECTRICAL CHARACTERISTICS

(V_{DD}=15V, V_{SS}=0V, V_{IC}=7.5V, R_L=10kΩ to V_{DD}/2, Ta=25°C, unless otherwise noted.)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
• DC CHARACTERISTICS						
Maximum Output Voltage	V _{OH1}	R _L = 10kΩ	14.8	14.9	-	V
	V _{OH2}	I _{source} = 200mA	14.2	14.5	-	V
	V _{OL1}	R _L = 10kΩ	-	0.1	0.2	V
	V _{OL2}	I _{sink} = 200mA	-	0.5	0.8	V
Input Offset Voltage	V _{IO}	R _S = 50Ω	-	1	10	mV
Input Bias Current	I _B		-	1	-	pA
Input Offset Current	I _{IO}		-	1	-	pA
Large Signal Voltage Gain	A _V	V _O = 13V/2V, R _L =10kΩ	65	90	-	dB
Common Mode Rejection Ratio	CMR	V _{IC} = 0V → 7.5V V _{IC} = 7.5V → 15V	50	75	-	dB
Supply Voltage Rejection Ratio	SVR	V _{DD} = 6V → 18V	60	75	-	dB
Input Common Mode Voltage Range	V _{ICM}	CMR ≥ 50dB	0	-	15	V
Operating Current	I _{DD}	No Signal, R _L = open	-	7.0	9.0	mA
• AC CHARACTERISTICS						
Unity Gain Frequency	f _t	C _L = 10pF	-	3	-	MHz
Phase Margin	Φ _M	C _L = 10pF	-	50	-	deg
Equivalent Input Noise Voltage	V _{NI}	f = 1kHz, R _S = 100Ω	-	80	-	nV/√Hz
Total Harmonic Distortion+Noise	THD+N	G _V = 6dB, C _L = 10pF, f _{in} = 1kHz, P _O = 0.1W	-	0.02	-	%
Output Power	P _O	f _{in} =1kHz, C _L =10pF, THD≤5%	-	3	-	mW
Channel Separation	CS	f = 1kHz	-	120	-	dB
• TRANSIENT CHARACTERISTICS						
Output Peak Current	I _{OP}	(Note6)	-	1000	-	mA
Slew Rate	SR	G _V = 0dB, C _L = 10pF, V _{in} = 4Vpp, (Note7)	5	9	-	V/μs

(Note6) Output peak current is defined by the lower value of the output source current or output sink current.

(Note7) Slew rate is defined by the lower value of the rise or fall.

■ Application Notes

•Package Power, Power Dissipation and Output Power

IC is heated by own operation and possibly gets damage when the junction power exceeds the acceptable value called Power Dissipation P_D . The dependence of the NJU77902 P_D on ambient temperature is shown in Fig 1. The plots are depended on following two points. The first is P_D on ambient temperature 25 °C, which is the maximum power dissipation. And the second is 0W, which means that the IC cannot radiate any more. The second point derives from the relation that maximum junction temperature T_{Jmax} is the same as storage temperature T_{stg} . Fig.1 is drawn by connecting those points and by the definition that the P_D lower than 25 °C is constant. Therefore, the P_D is shown following formula as a function of the ambient temperature between those points.

$$\text{Dissipation Power } P_D = \frac{T_{j \max} - T_a}{\theta_{ja}} \text{ [W]} \quad (T_a = 25 \text{ }^\circ\text{C to } T_a = 150 \text{ }^\circ\text{C})$$

Where, θ_{ja} is heat thermal resistance which depends on parameters such as package material, frame material and so on. Therefore, P_D is different in each package.

While, the actual measurement of dissipation power on NJU77902 is obtained using following equation.

$$(\text{Actual Dissipation Power}) = (\text{Supply Voltage } V_{DD}) \times (\text{Supply Current } I_{DD}) - (\text{Output Power } P_o)$$

The NJU77902 should be operated in lower than P_D of the actual dissipation power.

To sustain the steady state operation, take account of the Dissipation Power and thermal design.

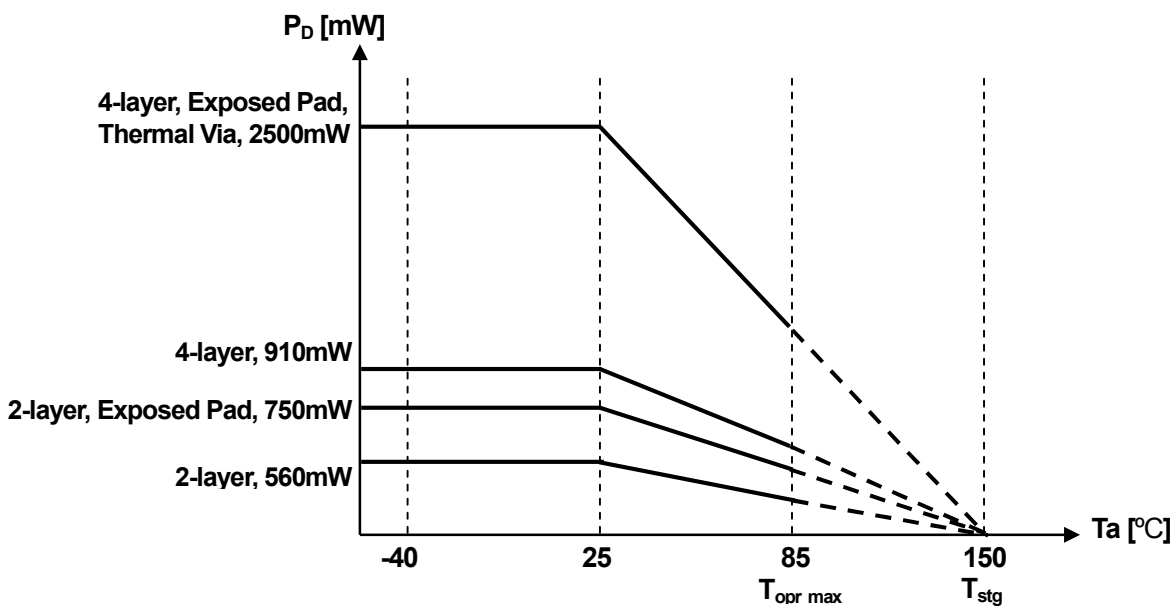
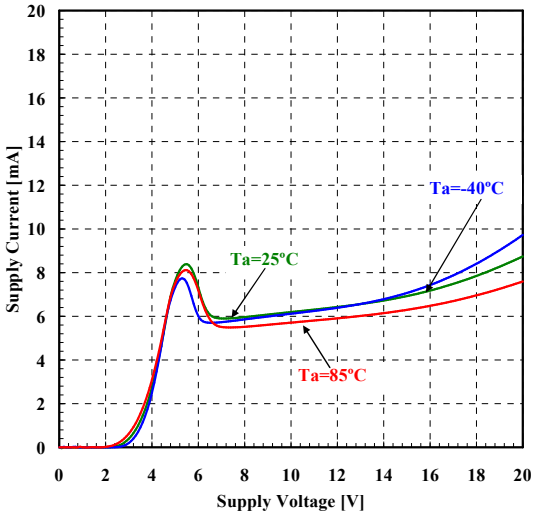


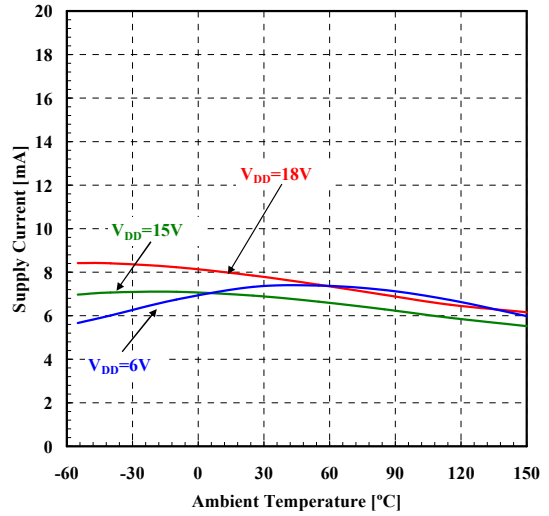
Fig1. Dependence of NJU77902 Power Dissipations on ambient temperature

■ TYPICAL CHARACTERISTICS

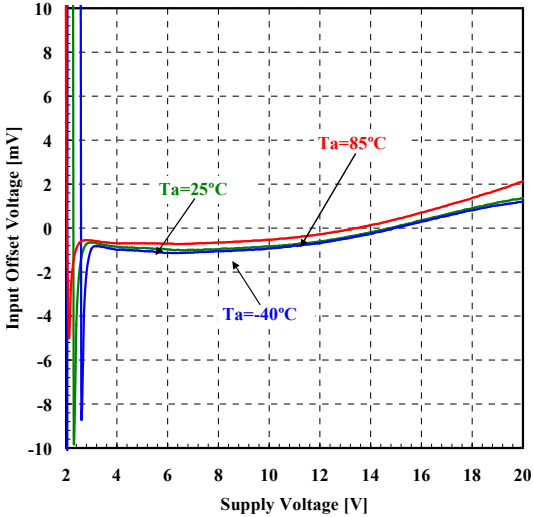
Supply Current vs. Supply Voltage
R_I=OPEN



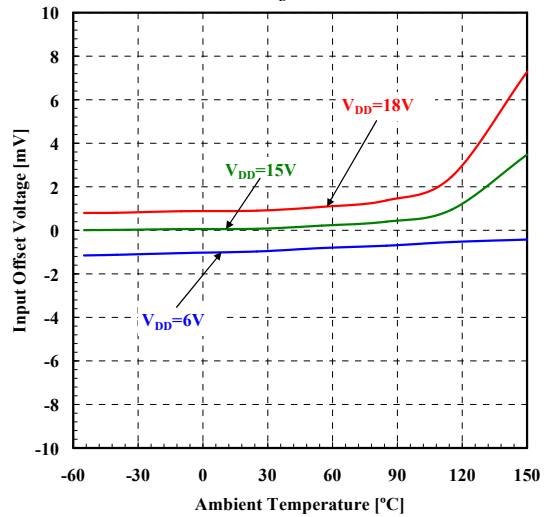
Supply Current vs. Ambient Temperature
R_I=OPEN



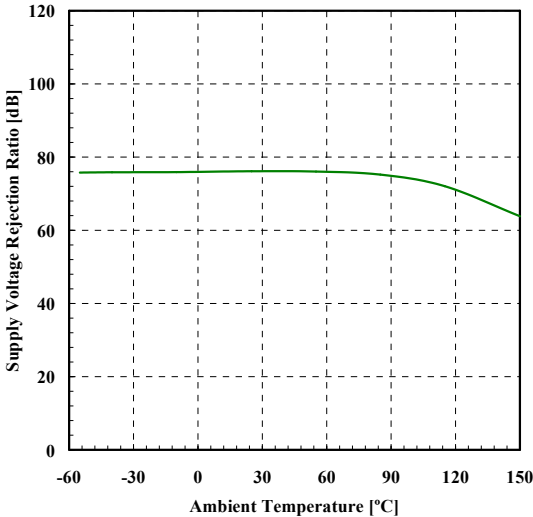
Input Offset Voltage vs. Supply Voltage
R_I=OPEN



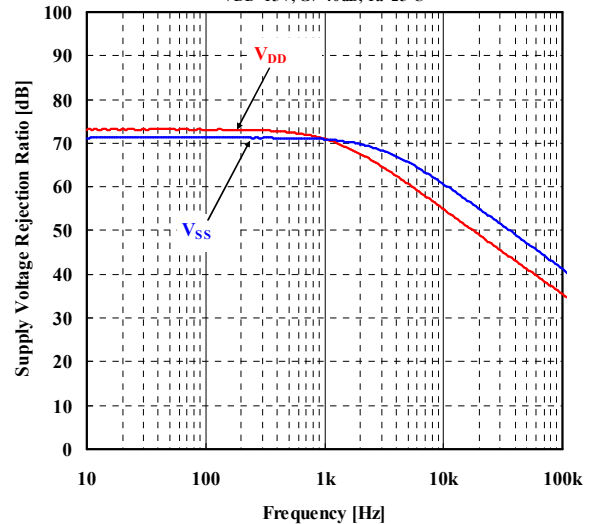
Input Offset Voltage vs. Ambient Temperature
R_I=OPEN

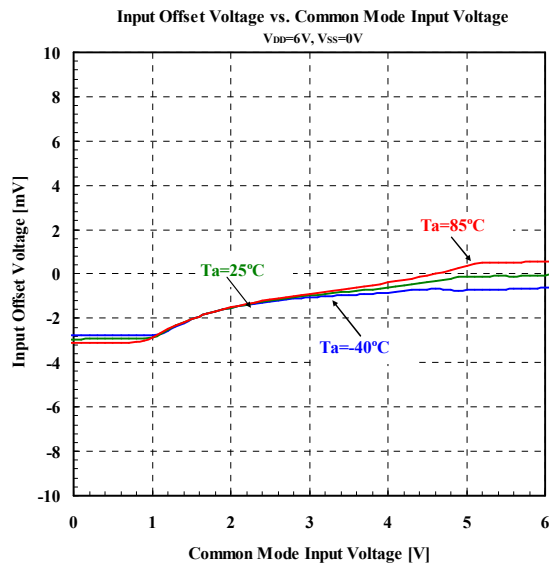
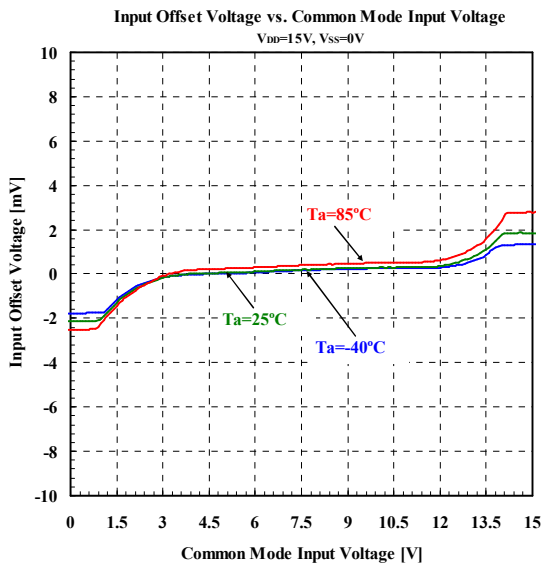
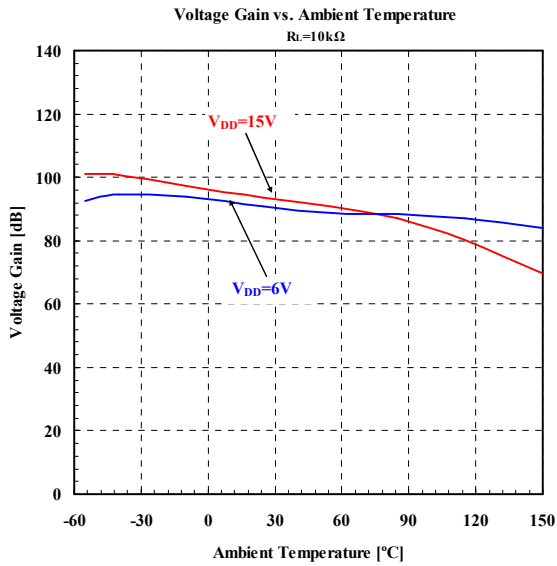
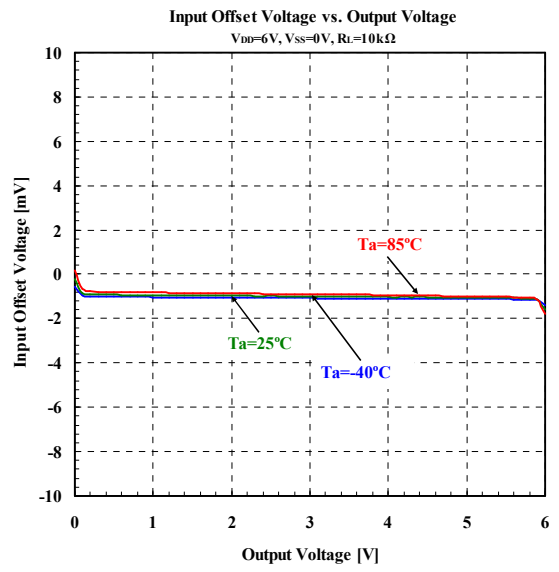
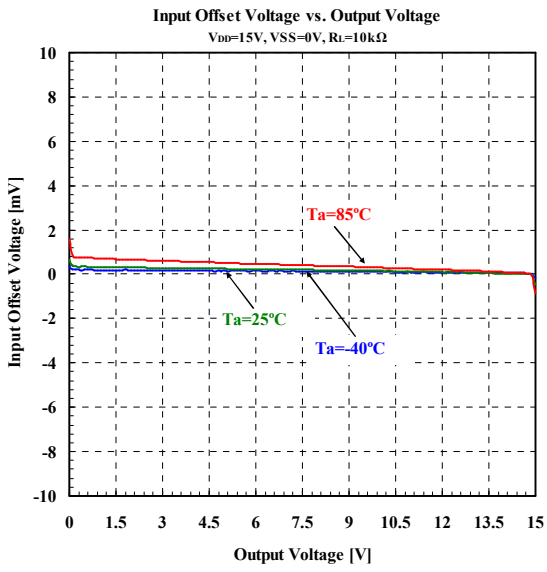


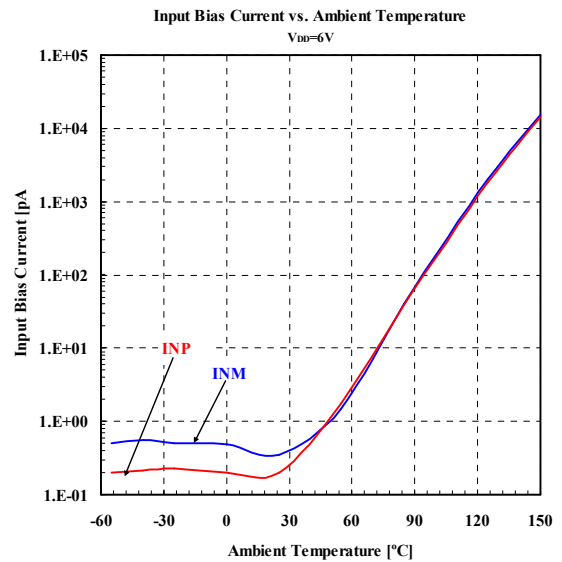
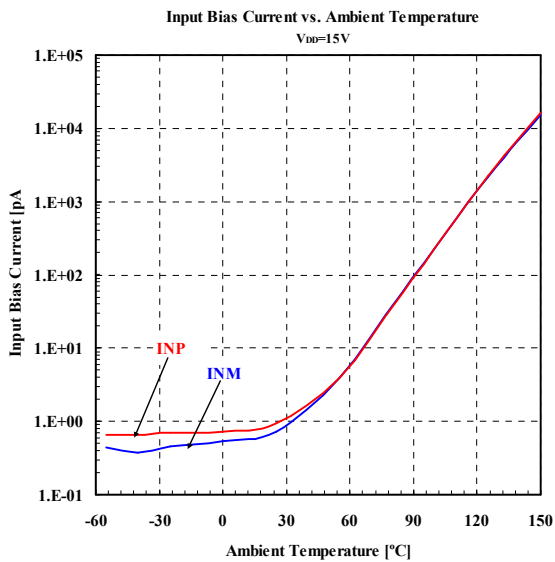
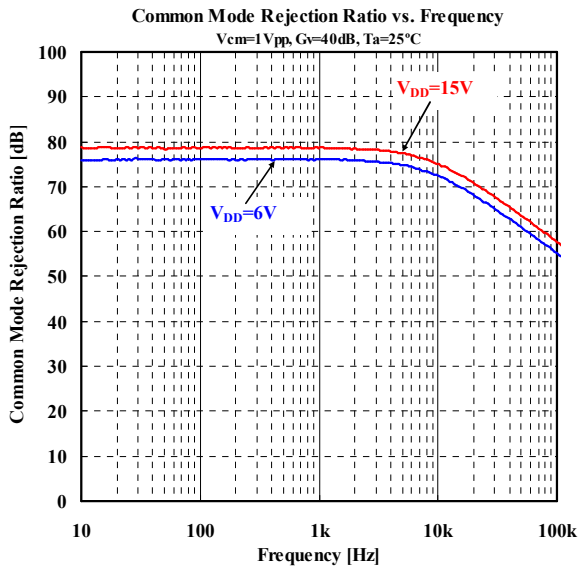
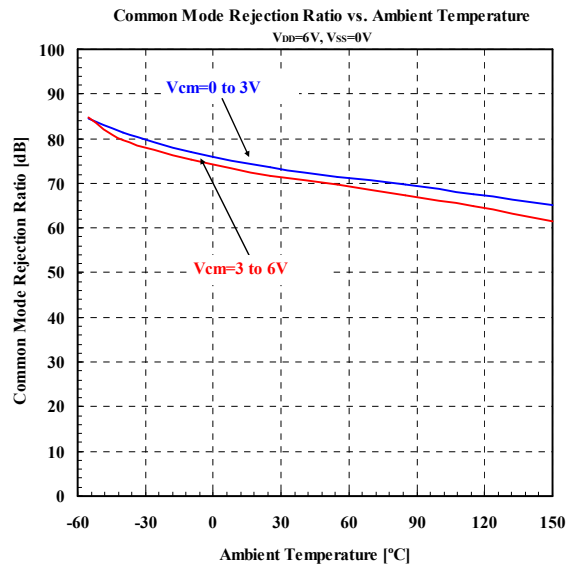
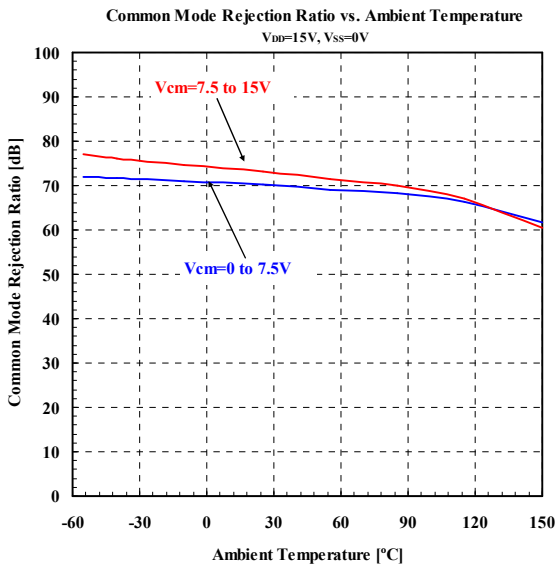
Supply Voltage Rejection Ratio vs. Ambient Temperature
R_I=OPEN

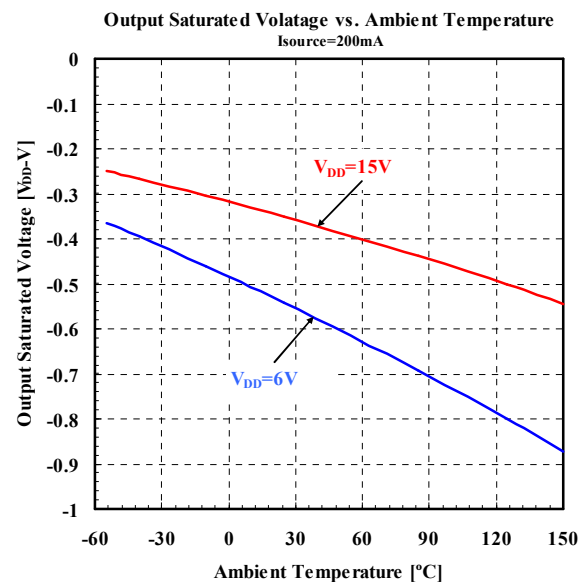
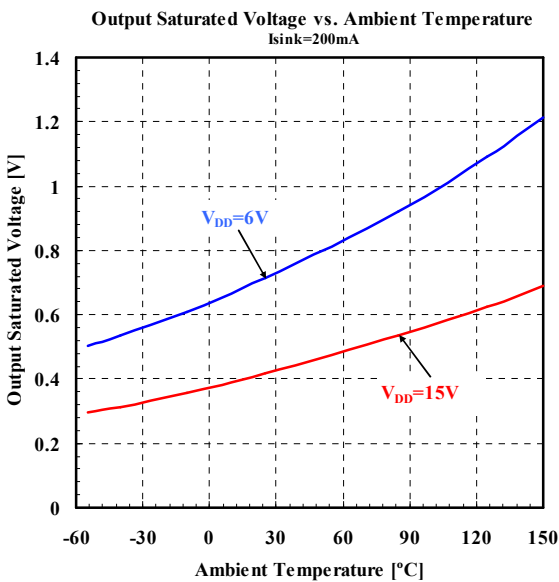
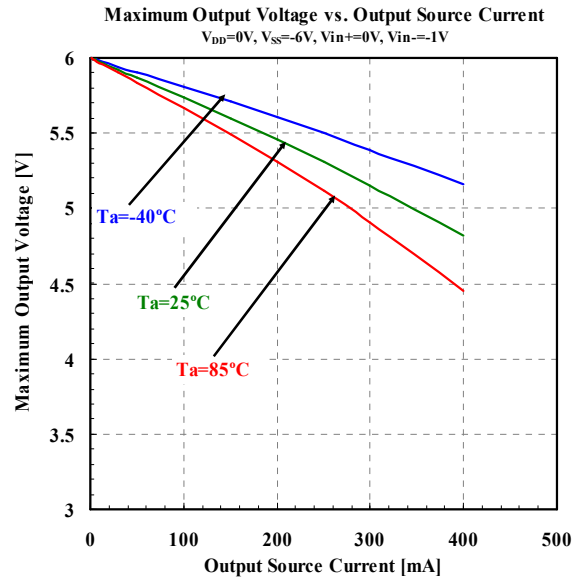
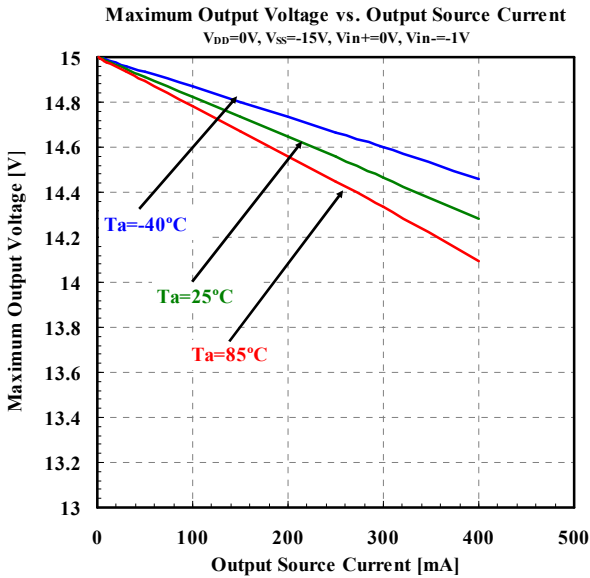
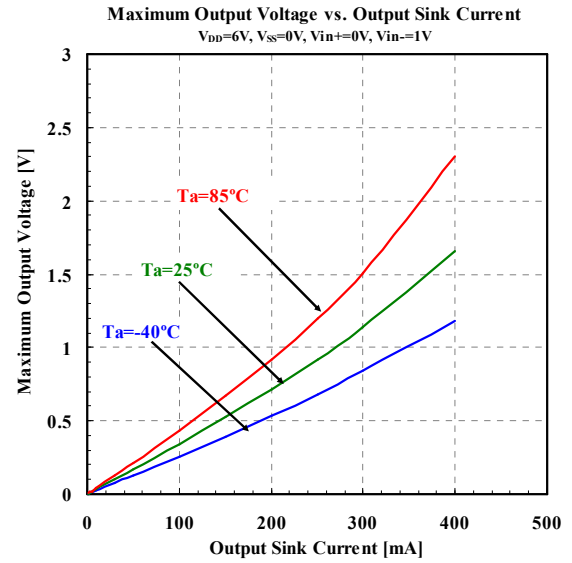
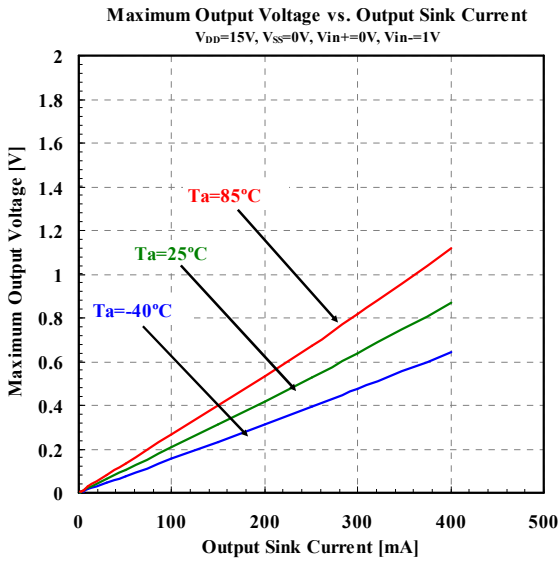


Supply Voltage Rejection Ratio vs. Frequency
V_{DD}=15V, G_v=40dB, T_a=25°C

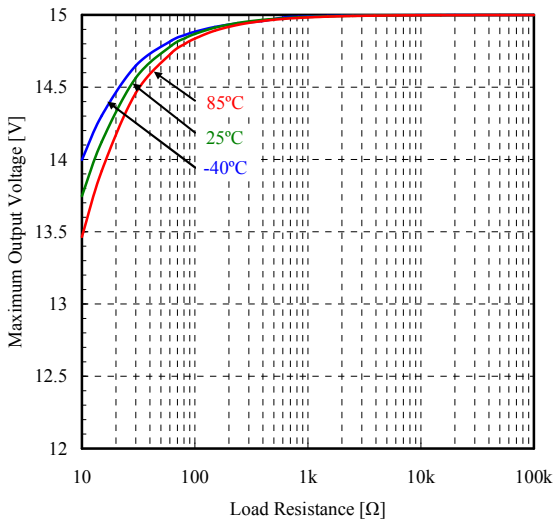




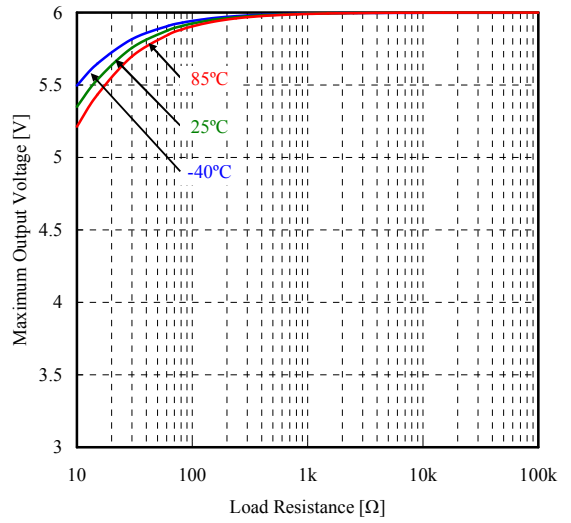




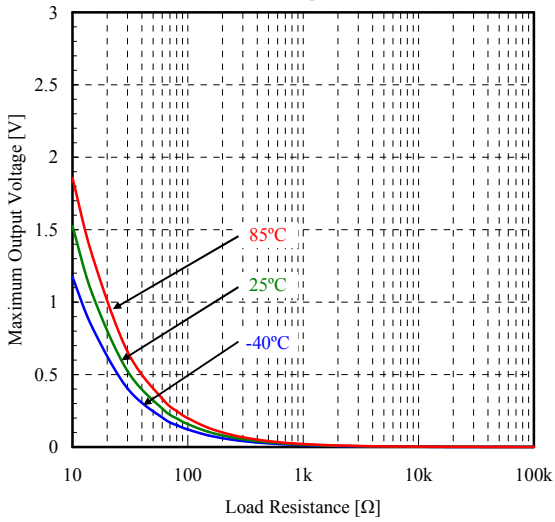
Maximum Output Voltage vs. Load Resistance
 $V_{DD}=15V, G_v=open, R_L \text{ to } 7.5V$



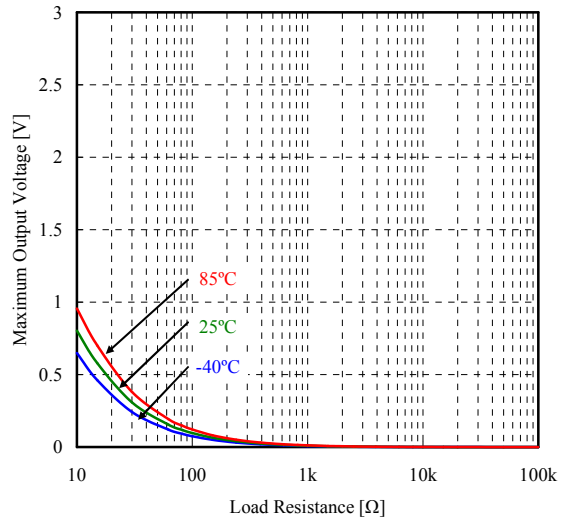
Maximum Output Voltage vs. Load Resistance
 $V_{DD}=6V, G_v=open, R_L \text{ to } 3V$



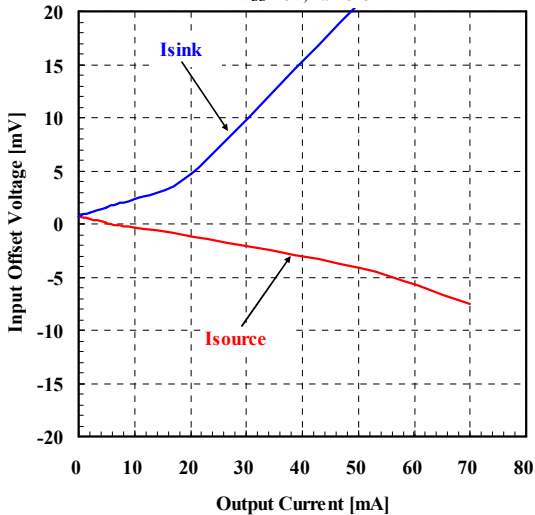
Maximum Output Voltage vs. Load Resistance
 $V_{DD}=15V, G_v=open, R_L \text{ to } 7.5V$



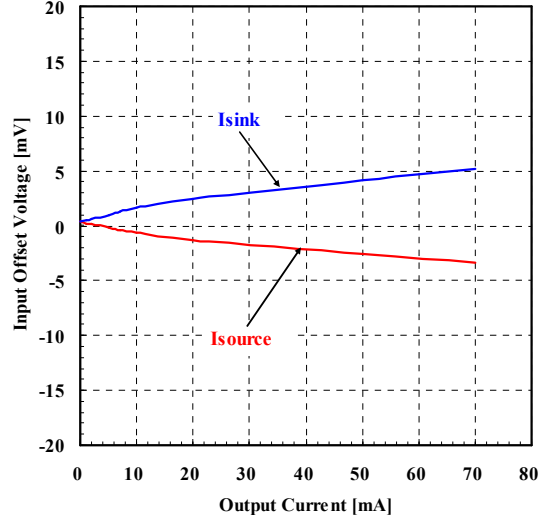
Maximum Output Voltage vs. Load Resistance
 $V_{DD}=6V, G_v=open, R_L \text{ to } 3V$

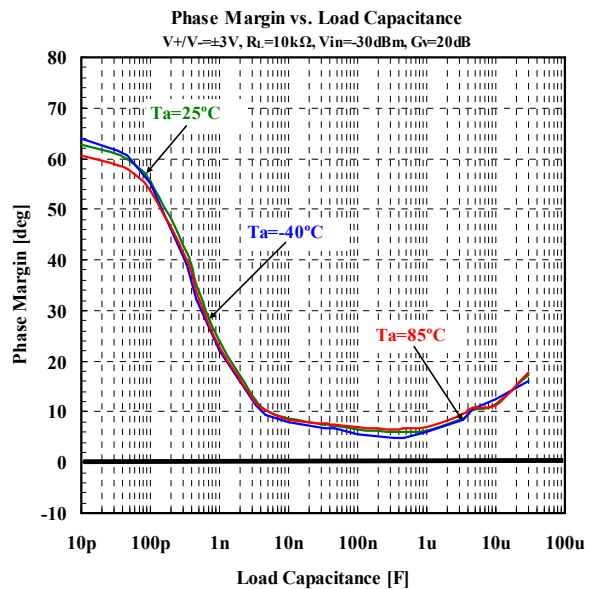
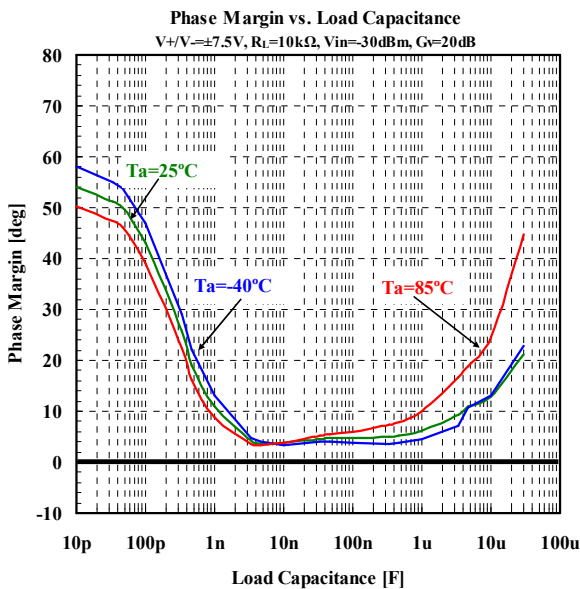
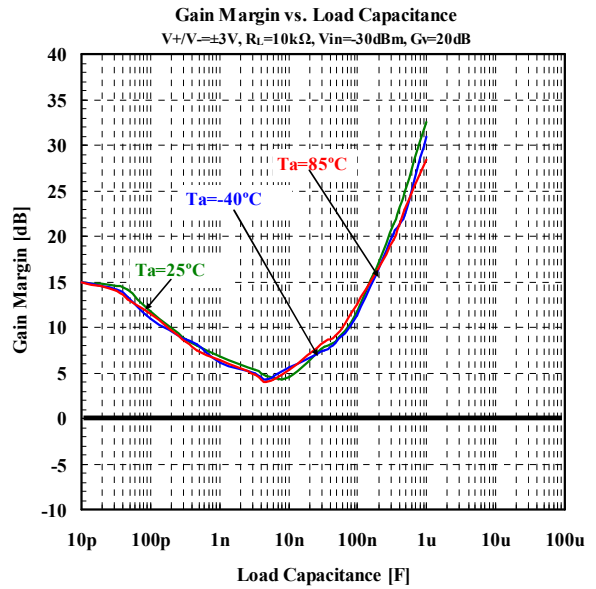
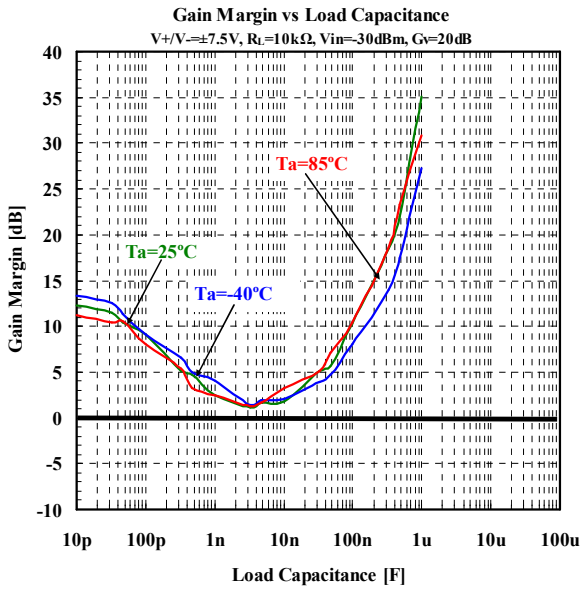
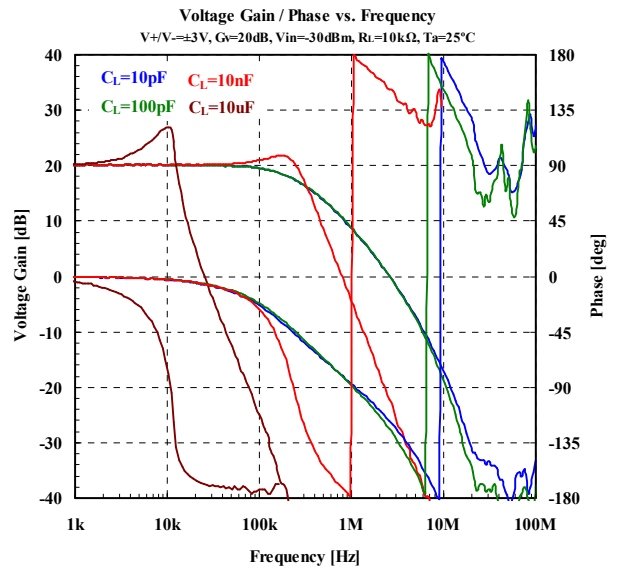
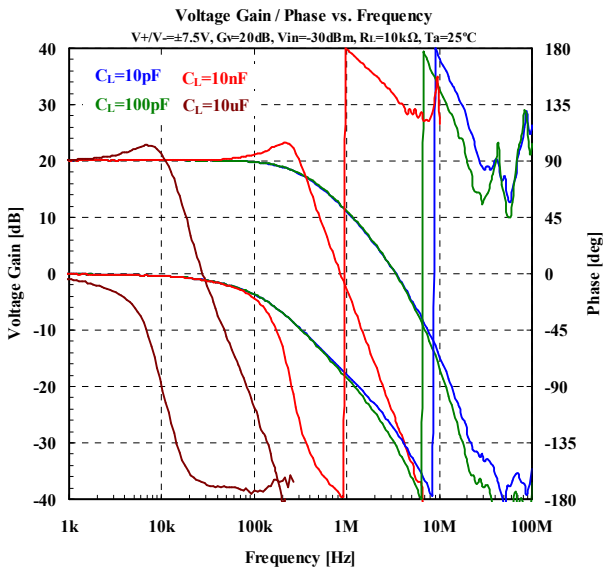


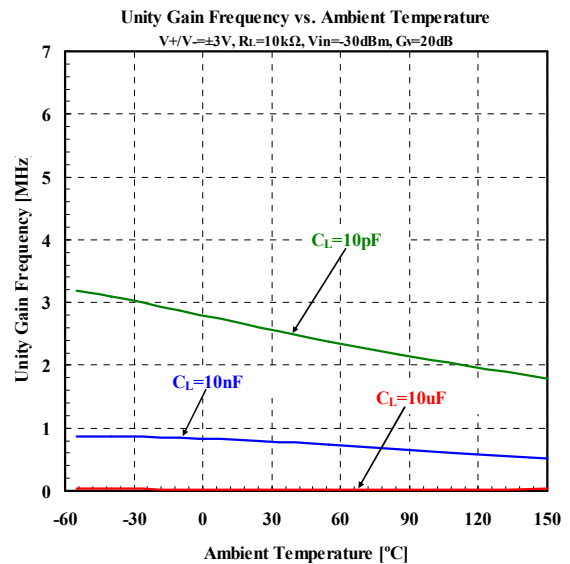
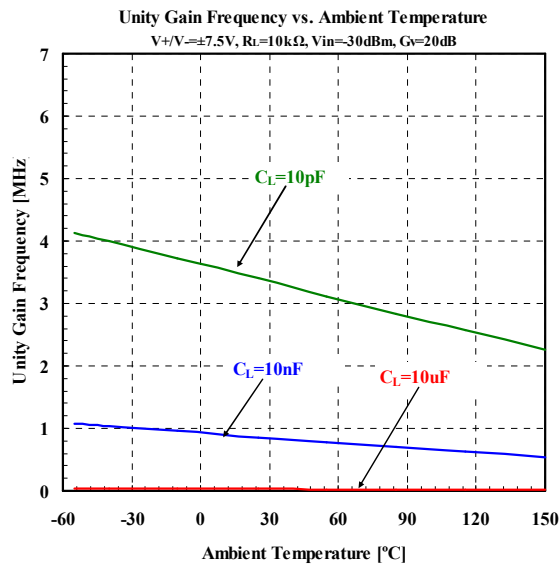
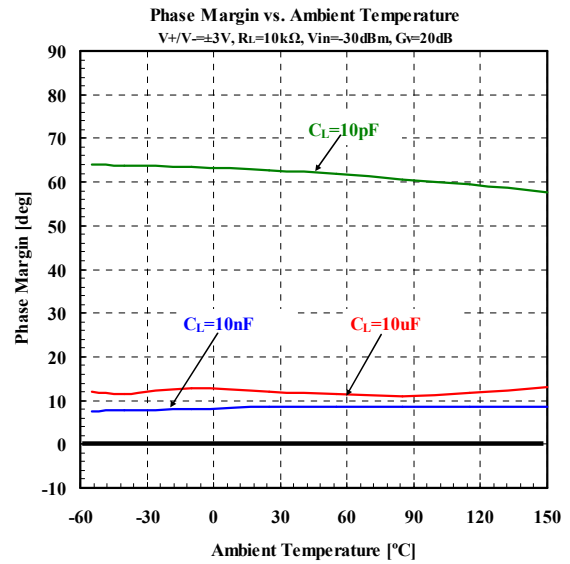
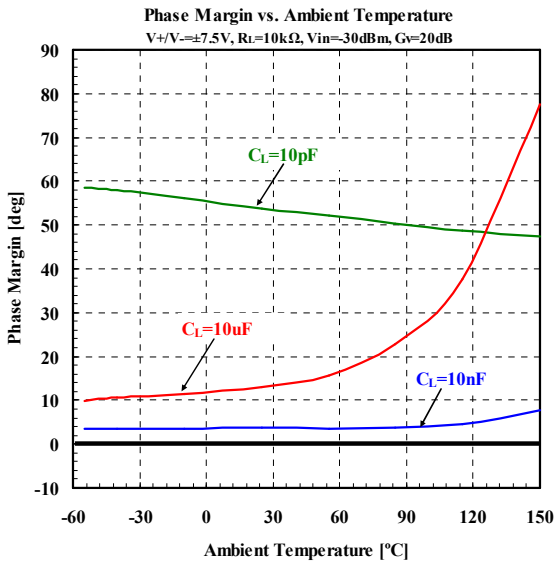
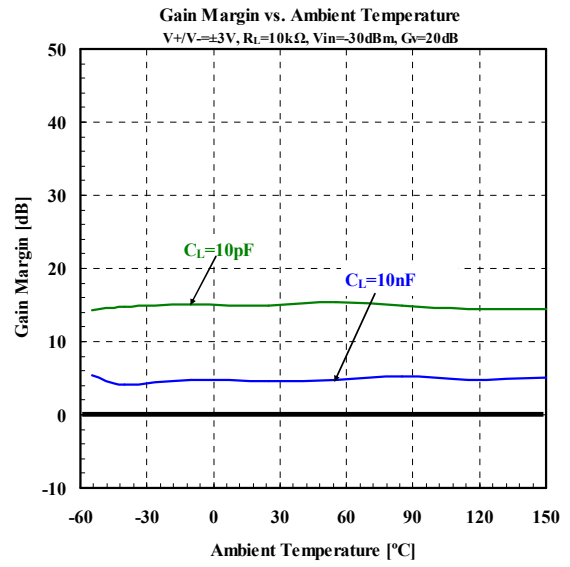
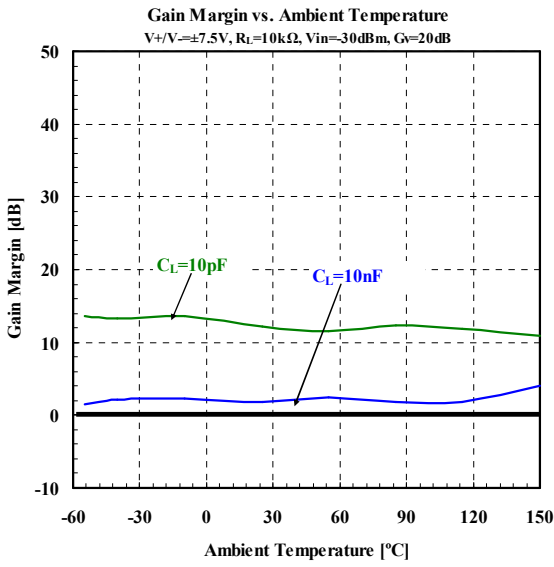
Input Offset Voltage vs. Output Current
 $V_{DD}=15V, T_a=25^\circ C$

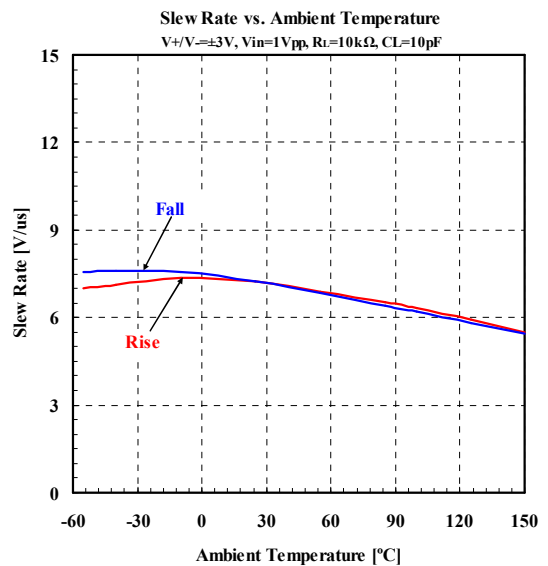
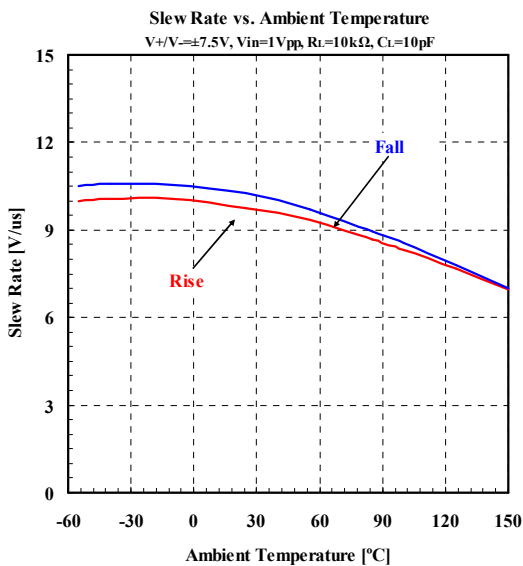
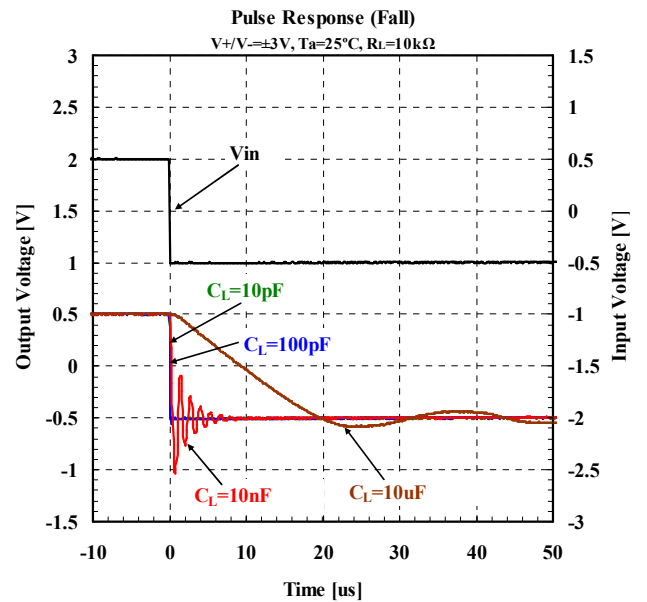
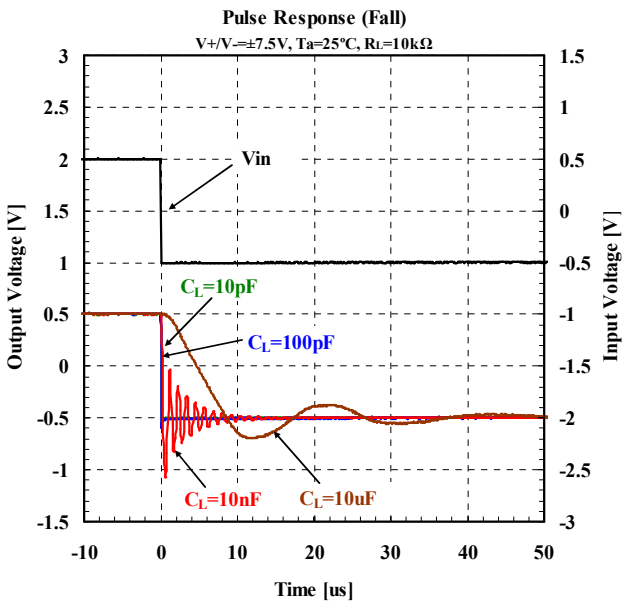
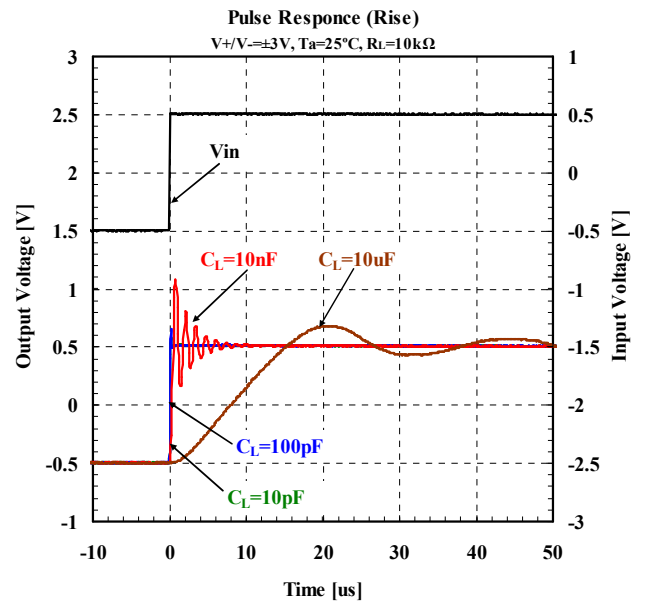
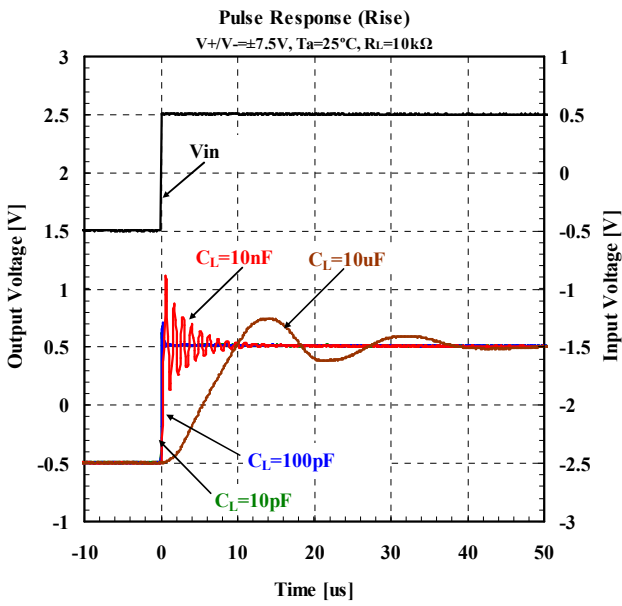


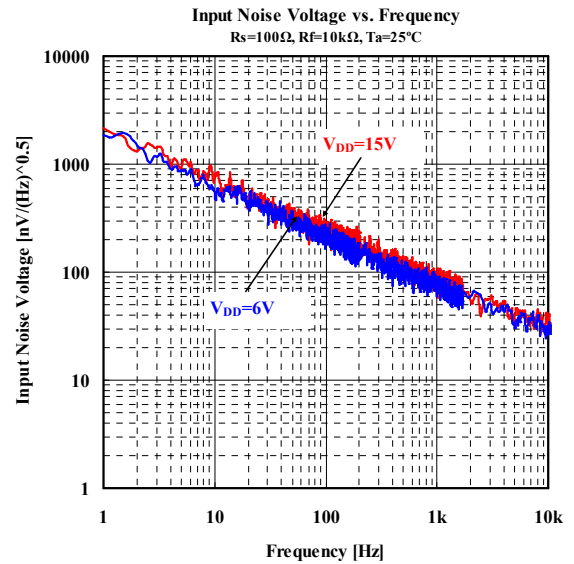
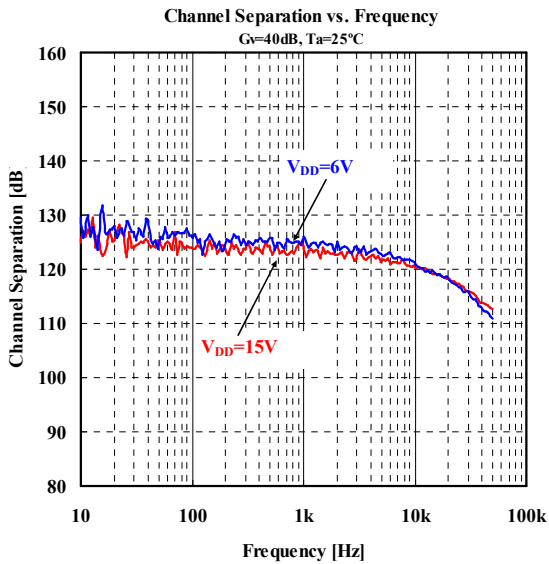
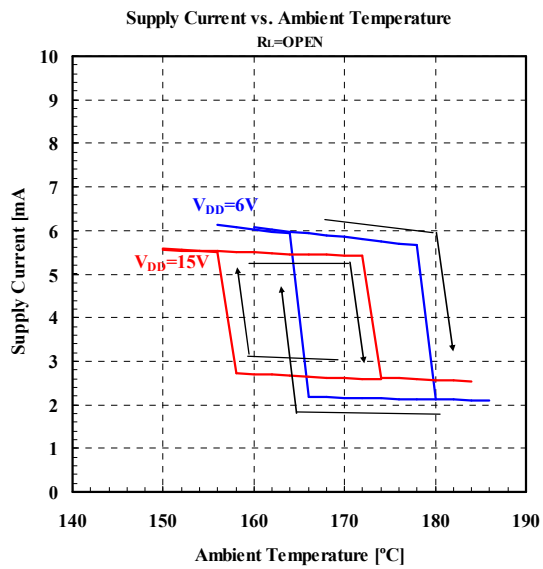
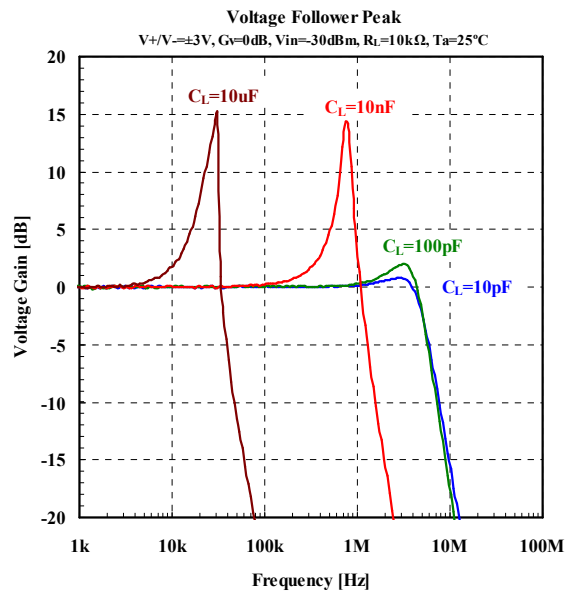
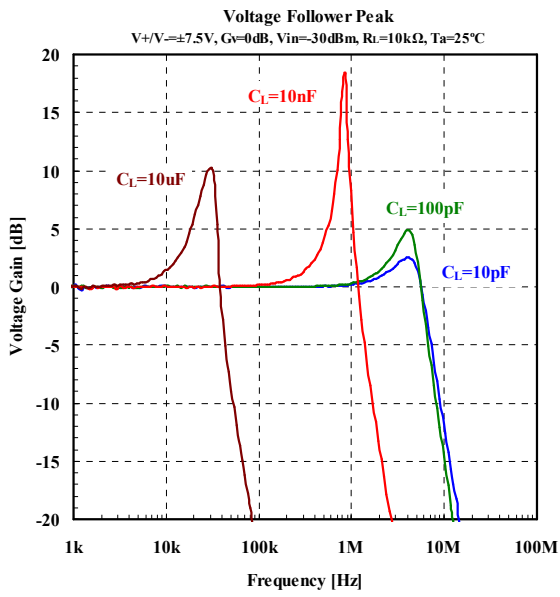
Input Offset Voltage vs. Output Current
 $V_{DD}=6V, T_a=25^\circ C$

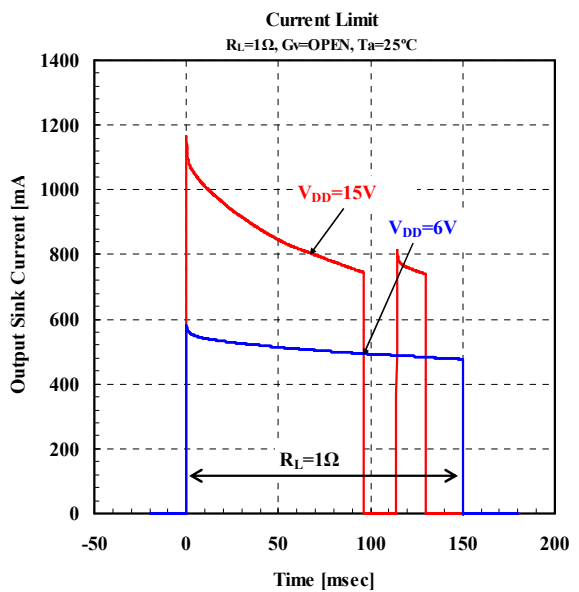
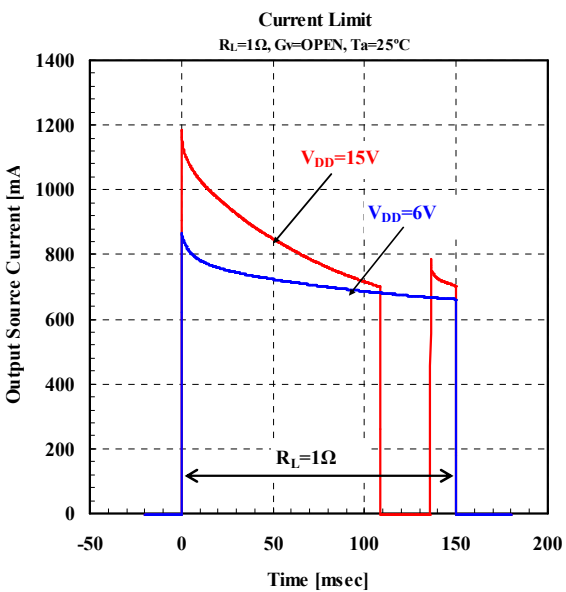
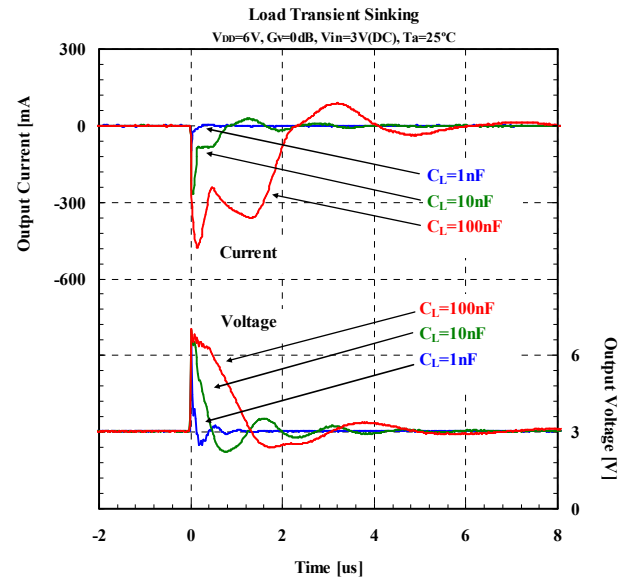
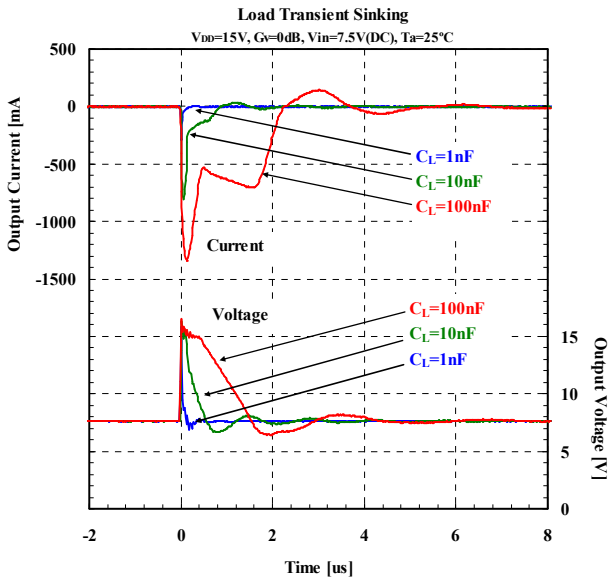
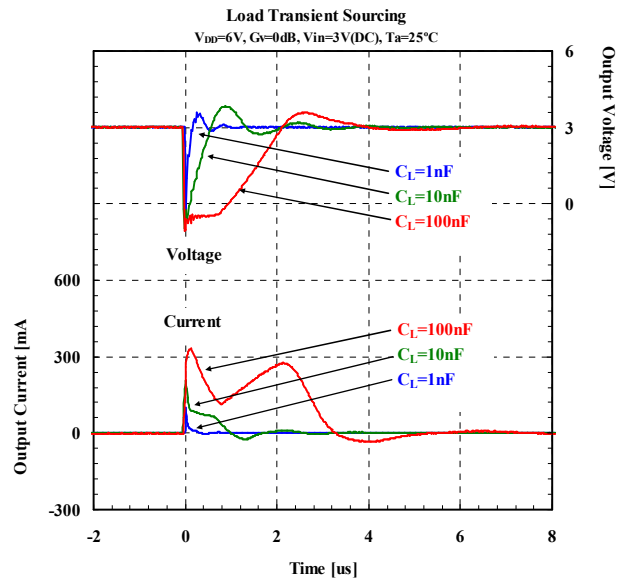
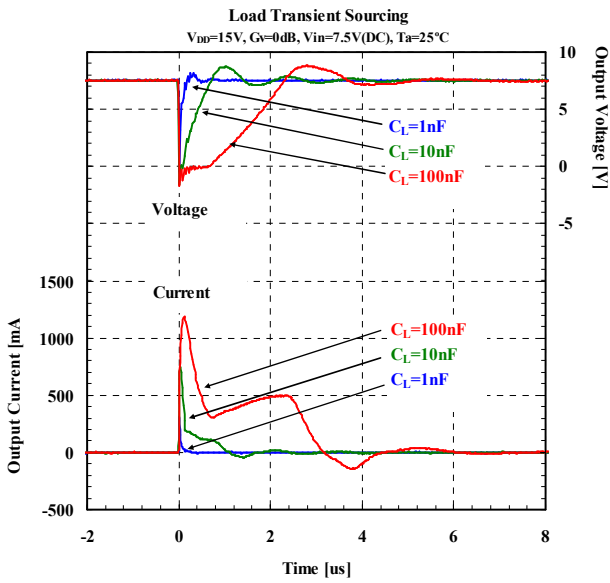


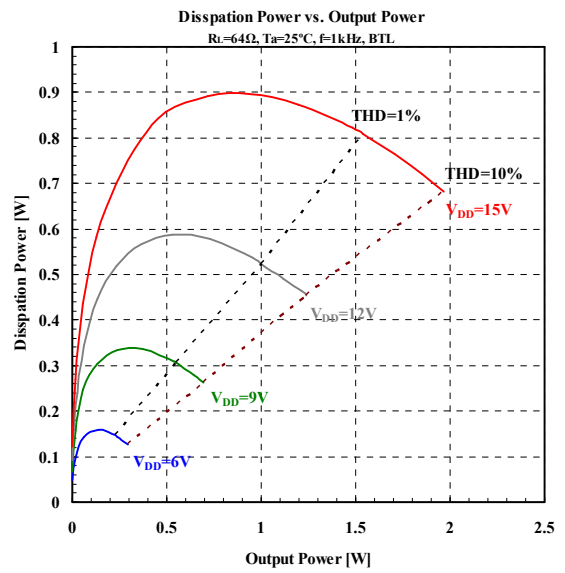
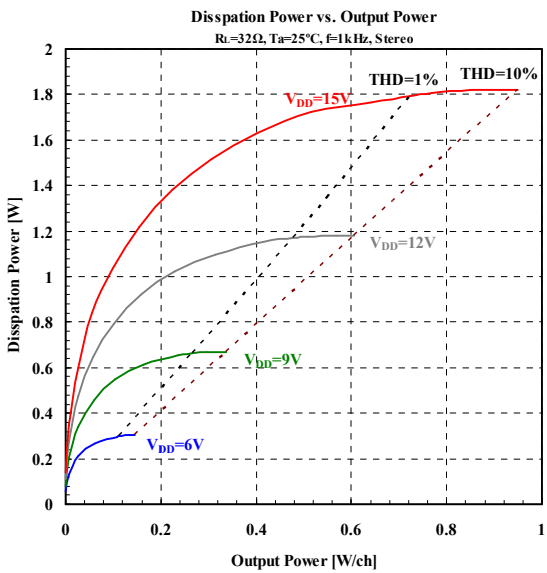
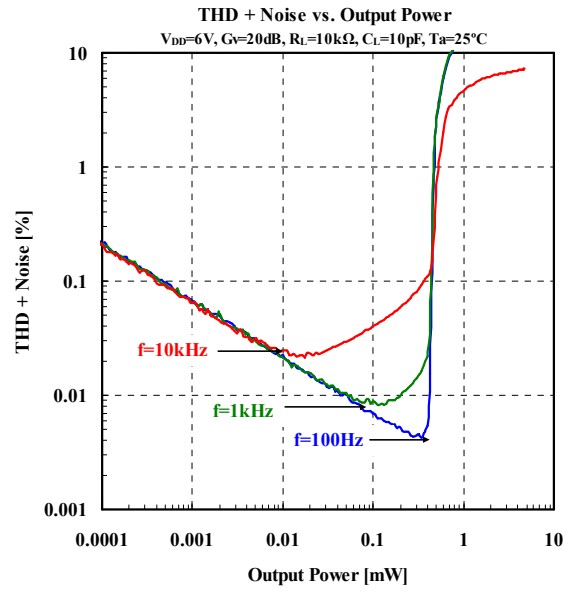
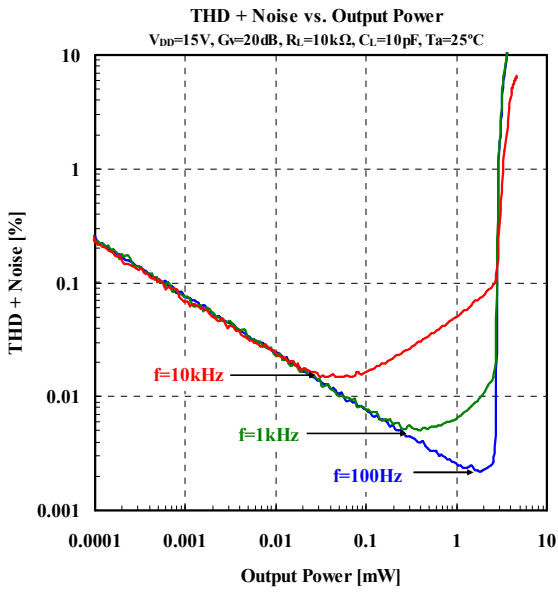












[CAUTION]

The specifications on this databook are only given for information, without any guarantee as regards either mistakes or omissions. The application circuits in this databook are described only to show representative usages of the product and not intended for the guarantee or permission of any right including the industrial rights.